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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of
Stephen E. Greco et al.

Serial No.: 09/725,862

Group Art Unit: 2815

Filed: November 30, 2000

Examiner: J. Nguyen

For: DUAL DAMASCENE FLOWABLE OXIDE INSULATION STRUCTURE
AND METALLIC BARRIER

1-15-02
T. Flowers

Commissioner of Patents and Trademarks
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. 1.111

Sir:

In response to the Office Action mailed August 1,
2001, please amend the above-identified application as
follows:

In the specification:

Please substitute the following paragraph for the
paragraph beginning at page 16, line 3. A marked up
copy of the paragraph showing current changes is
provided in an appendix to this response

B1

It should be noted that a protective layer will
also be formed on the first FOX layer 22 by reactive
ion etching with flouorocarbon gases (RIE). Since those
of skill in the art often etch a trench such as the
conductor troughs 26a and 26b by a fluorocarbon RIE, it
should be apparent that first oxidized sidewalls 37-40
may be formed during etching of the conductor troughs
26a and 26b. However, as previously mentioned, it is
preferred to form the first oxidized sidewalls 37-40 in
a separate step because a greater degree of control is